

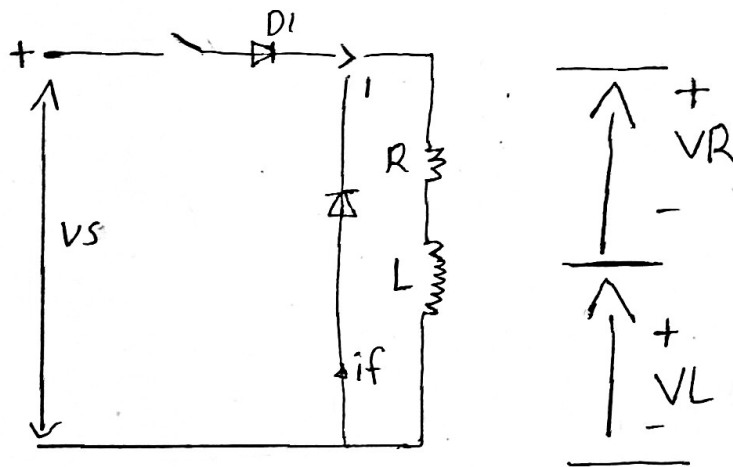
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Subject: P.E

Question no: 1 (a part)

Solution:

A diode circuit with an RL load.



When switch s_1 is closed at $t = 0$ the current through the inductor increase and is expressed as

$$V_s = V_L + V_R = L \frac{di}{dt} + Ri$$

With the initial $i(t=0) = 0$ $i(t)$ is expressed as

$$i(t) = \frac{V_s}{R} (1 - e^{-tR/L})$$

the initial rate of rise of the current at $t = 0$ is obtained

$$\left. \frac{di}{dt} \right|_{t=0} = \frac{V_s}{L}$$

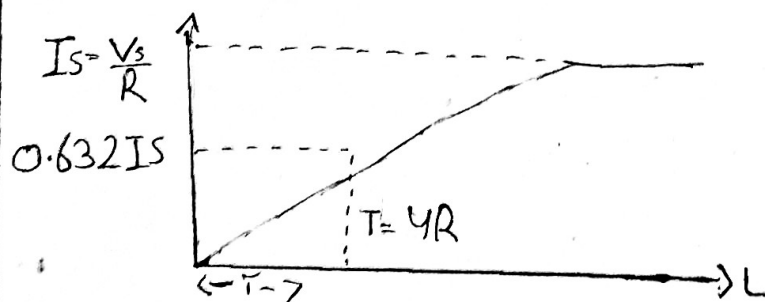
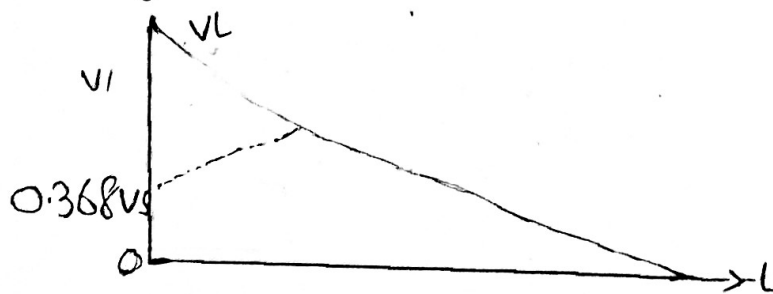
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The voltage across the inductor is

$$V_L(t) = L \frac{di}{dt} = V_s e^{-tR/L}$$

When $L/R = \tau$ is the time constant of an RL Load. The wave forms for the voltage and current.



Free wheeling Diode

→ A Free wheeling diode is basically a diode connected across the inductive load terminals to prevent the development of high voltage across the switch.

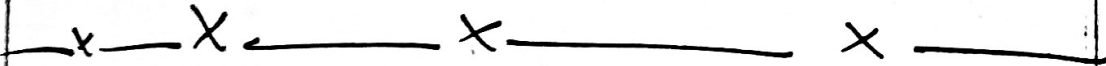
→ When the inductive circuit is switched off this diode gives a short circuit

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Path for the flow of inductor decay current and hence dissipation of stored energy in the inductor.

→ This diode is also called flywheel fly back diode.



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Question no: 1 (b part)

Given Data.

$$V_{DS} = 45V$$

$$V_T = 5V$$

Find $V_{as} =$ Solution:

If we know the.

Where for saturation

$$V_{DS} \geq V_{as} - V_T$$

$$V_{DS} = V_{as} - V_T$$

$$V_{DS} = V_{as} - V_T$$

Where

$$V_{as} = V_{DS} + V_T$$

Putting value.

$$V_{as} = 45 + 5$$

$$\{V_{as} = 50V\} \text{ Ans.}$$

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Question no. 2. a PartAnswer:

A Power electronic appliance of 500W 220V 50Hz rating is using a Power mosfet for switching purpose. The Power mosfet is replaced with power bipolar junction transistor its effect on his Performance and losses and efficiency on the appliance. The switching frequency will be lower of appliance because mosfet have high switching frequency the Bio Polar junction transistor.

The losses will be low because losses in BJT is less than Mosfet have high switching frequency than BJT Loss in appliance will be low another reason losses.

The BJT cannot operate at high frequency one of the impact on performance 500KHz on state voltage law for Bjt so the frequency of the impact on Performance the switching losses will increase due to Bjt in appliance. But conduction losses will be decrease because of Bjt replace mosfet appliance.

x — x — x — x —

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Question no 2.

B Part.

Answer:

The above appliance 2a if the mosfet replaced with SCR as switch and impact its performance losses and efficiency is given. The SCR have no capabilities to handle high frequencies and will impact on its performance losses and efficiency.

The SCR can handle more power voltage current which increase the efficiency of the appliance and one of the advantages efficiency.

The SCR can Protected because of the fuse, which can decrease losses used as the performance of the appliance improve.

→ x → x → x → x →

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Question no: 3.

Given data:

Range 8 to 40.

$$R_C = 45 \Omega$$

$$V_{CC} = 44.5 \text{ V}$$

$$V_D = 10 \text{ V}$$

$$V_{CE} = 1 \text{ V}$$

$$V_{BE} = 1.5 \text{ V}$$

Solution:

$$I_{CS} = \frac{V_{CC} - V_{CE}(\text{sat})}{R_C}$$

$$= \frac{44.5 - 1}{45} = 9.8 \text{ A}$$

$$I_{BS} = \frac{I_{CS}}{\beta_{\text{min}}}$$

$$= \frac{9.8 \text{ A}}{8} = 1.2 \text{ A}$$

$$I_B = 0.07 \times I_{BS}$$

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$$= 5 \times 1.2$$

$$I_B = 6 \text{ A}$$

$$I_B = \frac{V_B - V_{BE}(\text{sat})}{R_B}$$

$$R_B = \frac{V_B - V_{BE}(\text{sat})}{I_B}$$

$$R_B = \frac{10\text{V} - 1.5\text{V}}{6}$$

$$R_B = 1.4 \Omega$$

$$\beta_F = \frac{I_{CS}}{I_B}$$

$$= \frac{9.8}{6}$$

$$\beta_F = 1.6$$

$$P_T = V_{BE} I_B + V_{CE} I_C$$

$$P_T = 1.5 \times 6 + 1 \times 9.8$$

$$P_T = 18.8 \text{ Ans}$$